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Peter J. Geiss et al.

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*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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		Becker et al., LOW RESISTANCE POLYCRYSTALLINE SILICON BY BORON OR ARSENIC IMPLANTATION AND THERMAL CRYSTALLIZATION OF AMORPHOUSLY DEPOSITED FILMS, J. Appl. Phys., Vol. 56, No. 4, 15 August 1984, pages 1233-1236
NB		Carbone et al., "Correlation of Ellipsometric Vol. Fraction to Polysilicon Grain Size from Transmission Electron Microscopy", Sept. 1999, IEEE/SEMI Adv. Semiconductor Mfg. Conf. and Workshop, pp. 359-367.

EXAMINER  
Nema Berezny

DATE CONSIDERED  
4-16-05

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